

ABSTRACT OF THE DISCLOSURE

The principal surface of a substrate made of group III-V compound semiconductor is about (100) plane. A light emitting lamination structure is disposed on the principal surface. The light emitting lamination structure

5 includes a quantum well layer made of group III-V mixed crystal semiconductor containing In, a pair of carrier confinement layers made of semiconductor material having a band gap wider than the quantum well layer and sandwiching the quantum well layer, and a pair of clad layers made of semiconductor material having a band gap wider than the carrier confinement layers and sandwiching the

10 quantum well layer and the carrier confinement layers. A difference of 100 meV or larger exists between an energy level of the carrier confinement layers at a conduction band lower end and a ground level of an electron in the quantum well layer.